



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-15 A

Features

- R_{DS(ON)}, V_{GS}@-10V, I_D@-7.5A<68mΩ
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_{D}@-4A<85m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0105 ounces, 0.297grams

TO-252AA Drain Gate Source

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-60	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	T _C =25°C		-15		
	Tc=100°C	I _D	-9.5	A	
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	-60		
Power Dissipation	T _C =25°C	6	25	147	
	Tc=100°C	Po	10	W	
Continuous Drain Current(Note 4)	T _A =25°C	Ι _D	-4		
	T _A =70°C		-3.2	Α	
Power Dissipation	T _A =25°C	Po	2	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy ^(Note 6)		Eas	31	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R _{eJC}	5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.63	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-7.5A	-	55	68	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	71	85	
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-60V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic ^(Note 7)						
Total Gate Charge	Q_g	V _{DS} =-30V, I _D =-7.5A, V _{GS} =-10V ^(Note 3)	-	17	-	nC
Gate-Source Charge	Q_{gs}		-	2.8	-	
Gate-Drain Charge	Q_gd		-	3.6	-	
Input Capacitance	Ciss	V _{DS} =-30V, V _{GS} =0V, f=1MHZ	-	879	-	pF
Output Capacitance	Coss		-	70	-	
Reverse Transfer Capacitance	Crss	I= IIVIMZ	-	47	-	
Turn-On Delay Time	td _(on)		-	8.4	-	
Turn-On Rise Time	t r	V_{DD} =-30V, I_{D} =-1A, V_{GS} =-10V, R_{G} =6 Ω (Note 3)	-	30	-	ns
Turn-Off Delay Time	td _(off)		-	52	-	
Turn-Off Fall Time	t _f	(1300)	-	16	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	Is		-	-	-15	А
Diode Forward Current						
Diode Forward Voltage	V _{SD}	Is=-1A, V _G s=0V	-	-0.73	-1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. L=0.1mH, I_{AS} =-25A, V_{GS} =-10V, V_{DS} =-25V, R_{G} =25 ohm.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

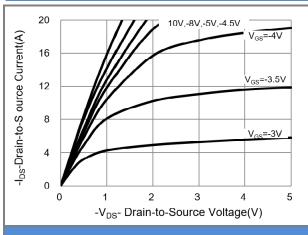


Fig.1 On-Region Characteristics

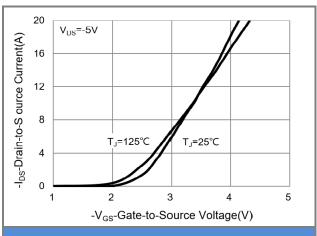


Fig.2 Transfer Characteristics

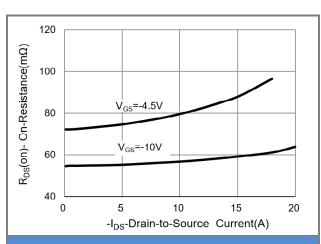


Fig.3 On-Resistance vs. Drain Current

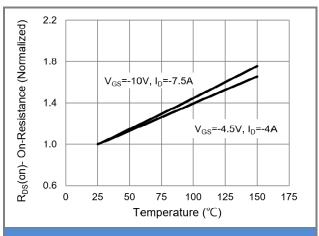


Fig.4 On-Resistance vs. Junction temperature

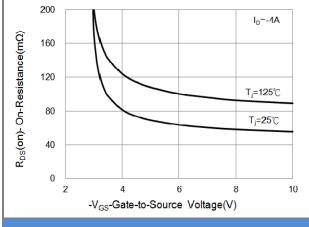


Fig.5 On-Resistance Variation with V_{GS}

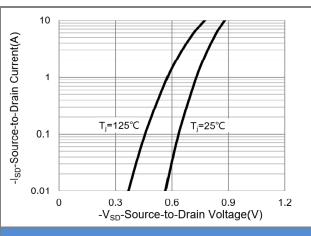


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

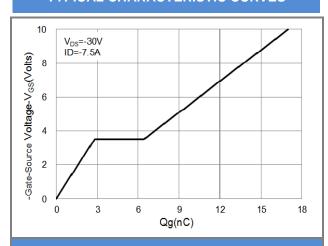


Fig.7 Gate-Charge Characteristics

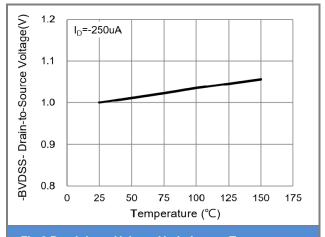


Fig.8 Breakdown Voltage Variation vs. Temperature

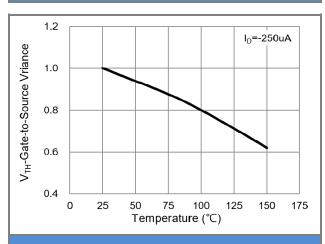


Fig.9 Threshold Voltage Variation with Temperature

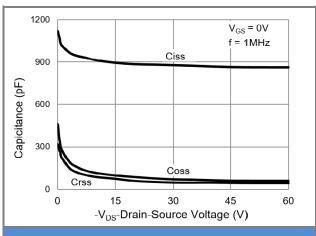


Fig.10 Capacitance vs. Drain-Source Voltage

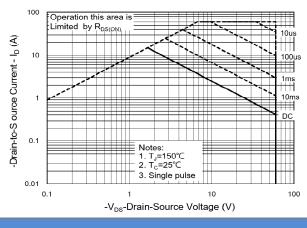


Fig.11 Maximum Safe Operating Area

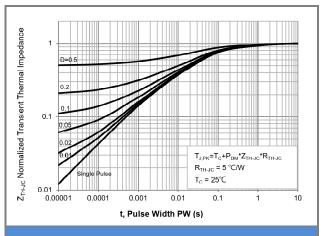


Fig.12 Normalized Thermal Transient Impedance

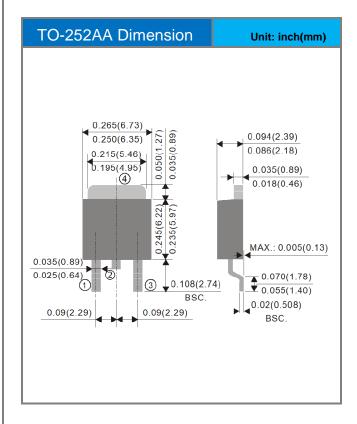


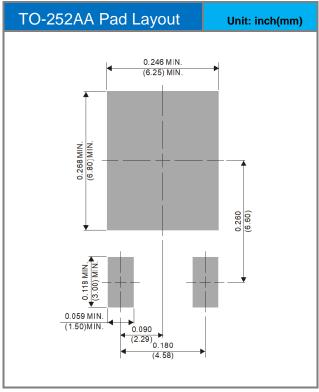


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJD15P06A-AU_L2_000A1	TO-252AA	3,000pcs / 13" reel	D15P06A	Halogen free

Packaging Information & Mounting Pad Layout









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